

Anisotropic properties of high - te superconducting YBCO films grown on SrTiO₃ (110) substrates

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ABSTRACT

We studied the anisotropic properties of High-Tc superconducting YBa₂Cu₃O₇-_x (YBCO) films grown on SrTiO₃ (110) substrates. The YBCO films were characterized by X-Ray diffraction, the atomic force microscope (AFM), and resistivity measurement. We researched the upper critical field (H_{c2}) and the pinning potential energy (U) in the different direction. The critical temperature (T_c) was decreasing with the field was increasing. As the anisotropic angle increased, the plot of H_{c2} vs T_c curves of films showed downward straight lines. The pinning potential energy was decreasing as the field was increasing.

Keywords : High-Tc superconductor、critical temperature、upper critical field、pinning potential energy

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